

Inchange Semiconductor

Product Specification

Silicon PNP Power Transistors

2SA1788

DESCRIPTION

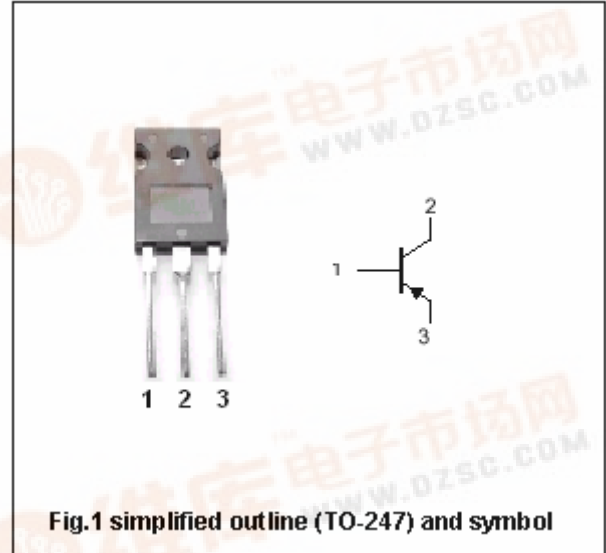
- With TO-247 package
- Complement to type 2SC4652

APPLICATIONS

- For audio output applications

PINNING

| PIN | DESCRIPTION |
|-----|--------------------------------------|
| 1 | Base |
| 2 | Collector;connected to mounting base |
| 3 | Emitter |



Absolute maximum ratings(Tc=25°C)

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|------------------|-----------------------------|----------------------|---------|------|
| V _{CBO} | Collector-base voltage | Open emitter | -120 | V |
| V _{CEO} | Collector-emitter voltage | Open base | -120 | V |
| V _{EBO} | Emitter-base voltage | Open collector | -5 | V |
| I _C | Collector current | | -8 | A |
| P _C | Collector power dissipation | T _C =25°C | 80 | W |
| T _j | Junction temperature | | 150 | °C |
| T _{stg} | Storage temperature | | -55~150 | °C |

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CHARACTERISTICS

T_j=25°C unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---|------|------|------|------|
| V _{(BR)CEO} | Collector-emitter breakdown voltage | I _C =-25mA; I _B =0 | -120 | | | V |
| V _{(BR)CBO} | Collector-base breakdown voltage | I _C =-1mA; I _E =0 | -120 | | | V |
| V _{(BR)EBO} | Emitter-base breakdown voltage | I _E =-1mA; I _C =0 | -5 | | | V |
| V _{CEsat} | Collector-emitter saturation voltage | I _C =-6A; I _B =-0.6 A | | | -2.0 | V |
| V _{BEsat} | Base-emitter saturation voltage | I _C =-6A; I _B =-0.6 A | | | -2.5 | V |
| I _{CBO} | Collector cut-off current | V _{CB} =-120V; I _E =0 | | | -10 | μ A |
| I _{EBO} | Emitter cut-off current | V _{EB} =-5V; I _C =0 | | | -10 | μ A |
| h _{FE} | DC current gain | I _C =-1A ; V _{CE} =-5V | 60 | | 320 | |

◆ h_{FE} classifications

| D | E | F |
|--------|---------|---------|
| 60-120 | 100-200 | 160-320 |

